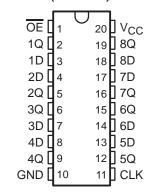
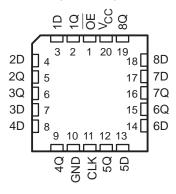
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- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static-Power Dissipation
- I_{off} and Power-Up 3-State Support Hot Insertion
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce)
 < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Package, and Ceramic (J) DIPs

SN54LVTH374 . . . J OR W PACKAGE SN74LVTH374 . . . DB, DW, OR PW PACKAGE (TOP VIEW)



SN54LVTH374 . . . FK PACKAGE (TOP VIEW)



description

These octal flip-flops are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The eight flip-flops of the 'LVTH374 devices are edge-triggered D-type flip-flops. On the positive transition of the clock (CLK) input, the Q outputs are set to the logic levels set up at the data (D) inputs.

A buffered output-enable (\overline{OE}) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

OE does not affect the internal operations of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

When V_{CC} is between 0 and 1.5 V, the devices are in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.



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description (continued)

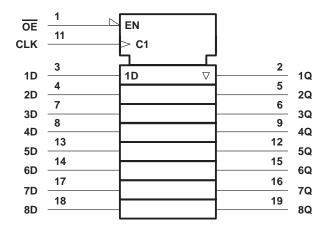
These devices are fully specified for hot-insertion applications using I_{off} and power-up 3-state. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

The SN54LVTH374 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH374 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE (each flip-flop)

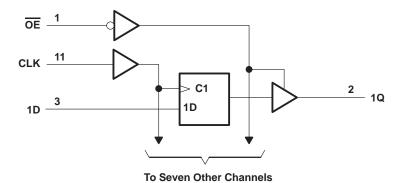
	OUTPUT		
OE	CLK	D	Q
L	1	Н	Н
L	\uparrow	L	L
L	H or L	Χ	Q_0
Н	Х	Χ	Z

logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	–0.5 V to 4.6 V
Input voltage range, V _I (see Note 1)	0.5 V to 7 V
Voltage range applied to any output in the high-impedance	
or power-off state, V _O (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the high state, V _O (see Note 1)	\dots -0.5 V to V _{CC} + 0.5 V
Current into any output in the low state, I _O : SN54LVTH374	96 mA
SN74LVTH374	
Current into any output in the high state, I _O (see Note 2): SN54LVTH374	48 mA
	64 mA
Input clamp current, I _{IK} (V _I < 0)	
Output clamp current, I _{OK} (V _O < 0)	
Package thermal impedance, θ _{JA} (see Note 3): DB package	115°C/W
DW package	97°C/W
PW package	
Storage temperature range, T _{stq}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 - 2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

		SN54LVTH374		SN74LVTH374		UNIT
		MIN	MAX	MIN	MAX	UNIT
Vcc	Supply voltage	2.7	3.6	2.7	3.6	V
VIH	High-level input voltage	2	J.	2		V
V _{IL}	Low-level input voltage		0.8		0.8	V
VI	Input voltage	į	5.5		5.5	V
IOH	High-level output current	4	-24		-32	mA
lOL	Low-level output current	32	48		64	mA
Δt/Δν	Input transition rise or fall rate	06	10		10	ns/V
Δt/ΔVCC	Power-up ramp rate	200		200		μs/V
TA	Operating free-air temperature	-55	125	-40	85	°C

NOTE 4: All unused control inputs of the device must be held at VCC or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			SN54LVTH374			SN74LVTH374				
PAI	RAMETER	TEST CONDITIONS			TYP†	MAX	MIN	TYP†	MAX	UNIT		
VIK		$V_{CC} = 2.7 \text{ V},$	I _I = -18 mA			-1.2			-1.2	V		
Voн		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V},$	I _{OH} = -100 μA	V _{CC} -0	.2		V _{CC} -0	.2				
		$V_{CC} = 2.7 \text{ V},$	I _{OH} = -8 mA	2.4			2.4			V		
		V _{CC} = 3 V	$I_{OH} = -24 \text{ mA}$	2						V		
		VCC = 3 V	$I_{OH} = -32 \text{ mA}$					2				
		V _{CC} = 2.7 V	I _{OL} = 100 μA			0.2			0.2			
		VCC = 2.7 V	I _{OL} = 24 mA			0.5			0.5			
Voi			I _{OL} = 16 mA			0.4			0.4	V		
VOL		VCC = 3 V	I _{OL} = 32 mA			0.5			0.5	V		
		VCC = 3 V	I _{OL} = 48 mA			0.55						
	_		$I_{OL} = 64 \text{ mA}$									
		$V_{CC} = 0 \text{ or } 3.6 \text{ V},$	V _I = 5.5 V			10			10			
ŧι	Control inputs	$V_{CC} = 3.6 \text{ V},$	$V_I = V_{CC}$ or GND			±1			μΑ			
''	Data innuta	V _{CC} = 3.6 V	$\Lambda^{I} = \Lambda^{CC}$		1			1				
	Data inputs	VCC = 3.0 V	V _I = 0		- 5		-5					
l _{off}		$V_{CC} = 0$,	V_I or $V_O = 0$ to 4.5 V		Q"				±100	μΑ		
	Data inputs	VCC = 3 V	V _I = 0.8 V	75	75							
l(hold)			V _I = 2 V	-75	-75 -75					μΑ		
n(noid)		V _{CC} = 3.6 V [‡] ,	V _I = 0 to 3.6 V	Q					500 -750	P 1		
lozh		V _{CC} = 3.6 V,	V _O = 3 V			5			5	μΑ		
lozL		V _{CC} = 3.6 V,	V _O = 0.5 V			- 5			- 5	μΑ		
lozpu		$\frac{V_{CC}}{OE} = 0$ to 1.5 V, $V_{O} = 0$	0.5 V to 3 V,			±100*			±100	μΑ		
lozpd		$\frac{V_{CC}}{OE} = 1.5 \text{ V to 0, V}_{O} = 0.5 \text{ Care}$	0.5 V to 3 V,			±100*			±100	μΑ		
		V _{CC} = 3.6 V,	Outputs high			0.19			0.19			
Icc		$I_{O} = 0$,	Outputs low 5				5	mA				
		VI = VCC or GND	Outputs disabled	1		0.19			0.19			
Δl _{CC} §		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$, One input at $V_{CC} - 0.6 \text{ V}$, Other inputs at V_{CC} or GND				0.2			0.2	mA		
Ci		V _I = 3 V or 0		3				pF				
Co		V _O = 3 V or 0		1	7			7		pF		
				_								

^{*} On products compliant to MIL-PRF-38535, this parameter is not production tested.



[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

[‡] This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

[§] This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

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timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

			SN54LVTH374				SN74LVTH374			
			V _{CC} = 3.3 V ± 0.3 V		2.7 V	V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
fclock	Clock frequency		150	.6.	150		150		150	MHz
t _W	Pulse duration, CLK high or low	3.3	~	3.3		3.3		3.3		ns
t _{su}	Setup time, data before CLK↑	1.6	o Po	2		1.5		2		ns
t _h	Hold time, data after CLK↑	0.8	8,	0.5		0.8	·	0		ns

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L = 50$ pF (unless otherwise noted) (see Figure 1)

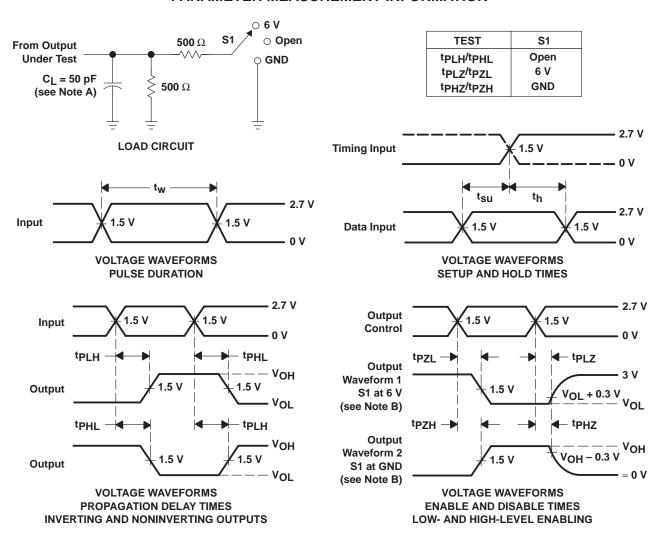
		SN54LVTH374				SN74LVTH374						
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V			V _{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f _{max}			150		150		150			150		MHz
t _{PLH}	CLK	Q	1.7	4.7	1/3	5.3	1.8	2.9	4.5		5	ns
t _{PHL}		CLK	l q	1.7	4.5	Wal	4.6	1.8	2.9	4.2		4.3
^t PZH	ŌĒ	Q	1.2	4.9		5.7	1.3	2.8	4.7		5.6	ns
t _{PZL}	OE	Q	1.5	4.8		5.4	1.6	3	4.7		5.2	115
^t PHZ	ŌĒ	Q	1.8	4.8		5	1.9	3	4.6		4.9	ns
tPLZ			1.9	4.9		5	2	3.1	4.5		4.6	115

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C.



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PARAMETER MEASUREMENT INFORMATION



NOTES: A. C₁ includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \ \Omega$, $t_f \leq 2.5 \ ns$.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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